

# ECE 2100 Lecture Notes 4/11/03

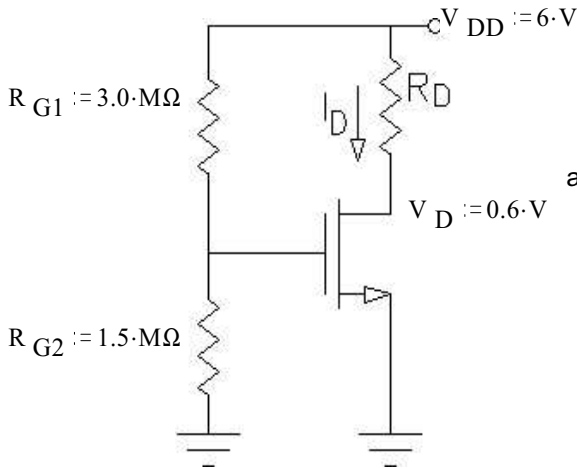
HW #20, due: W, 4/9

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4/10/03,  
4/17/03

Ex1 The transistor in the circuit shown has the following characteristics.

$$\mu_n \cdot C_{ox} = k'_n := 90 \cdot \frac{\mu A}{V^2} \quad \frac{W}{L} = 12$$

$$V_t := 0.8 \cdot V \quad \lambda := 0 \quad W := 12 \cdot L$$



$$I_D := k'_n \cdot \frac{W}{L} \cdot \left[ (V_{GS} - V_t) \cdot V_{DS} - \frac{1}{2} \cdot V_{DS}^2 \right]$$

b) What is the value of  $R_D$ ?

a) Find  $I_D$

$$V_G := \frac{R_{G2}}{R_{G1} + R_{G2}} \cdot V_{DD} \quad V_G = 2 \cdot V$$

$$V_{GD} := V_G - V_D \quad V_{GD} = 1.4 \cdot V > V_t = 0.8 \cdot V$$

Triode region

OR:

$$V_{GS} := V_G$$

$$V_{DS} := V_D$$

$$V_{DS} = 0.6 \cdot V < V_{GS} - V_t = 1.2 \cdot V$$

Triode region

$$I_D = 0.583 \cdot mA$$

$$R_D := \frac{V_{DD} - V_D}{I_D}$$

$$R_D = 9.26 \cdot k\Omega$$

Ex2 The transistor in the circuit shown has the following characteristics.

$$k'_n \cdot \frac{W}{L} = K := 3.0 \cdot \frac{mA}{V^2} \quad V_t := 1.8 \cdot V \quad \lambda := 0$$

a)  $V_{DD} = 10 \cdot V$  Find  $V_G$

$$V_G := \frac{R_{G2}}{R_{G1} + R_{G2}} \cdot V_{DD} \quad V_G = 3.197 \cdot V$$

$$V_G = 3.2 \cdot V$$

b) Find  $I_D$   $0 = \left[ R_S^2 \cdot I_D^2 - 2 \cdot \left[ (V_G - V_t) \cdot R_S + \frac{1}{K} \right] \cdot I_D + (V_G - V_t)^2 \right]$

$$a := R_S^2$$

$$b := -2 \cdot \left[ (V_G - V_t) \cdot R_S + \frac{1}{K} \right]$$

$$c := (V_G - V_t)^2$$

$$I_{D1} := \frac{-b + \sqrt{b^2 - 4 \cdot a \cdot c}}{2 \cdot a}$$

$$I_{D1} = 1.626 \cdot mA$$

$$I_{D2} := \frac{-b - \sqrt{b^2 - 4 \cdot a \cdot c}}{2 \cdot a}$$

$$I_{D2} = 0.534 \cdot mA$$

Try:  $V_{GS1} := V_G - I_{D1} \cdot R_S \quad V_{GS1} = 0.759 \cdot V < V_t = 1.8 \cdot V$  Doesn't make sense

$V_{GS2} := V_G - I_{D2} \cdot R_S \quad V_{GS2} = 2.397 \cdot V > V_t = 1.8 \cdot V$  OK,  $I_D := 0.5338 \cdot mA$

The equation only works in the SATURATION region, so check.  $V_D := V_{DD} - I_D \cdot R_D \quad V_D = 4.662 \cdot V$

$$V_{GD} := V_G - V_D \quad V_{GD} = -1.465 \cdot V < V_t = 1.8 \cdot V \quad \text{Saturation region}$$

OR:

$$V_S := I_D \cdot R_S$$

$$V_S = 0.801 \cdot V$$

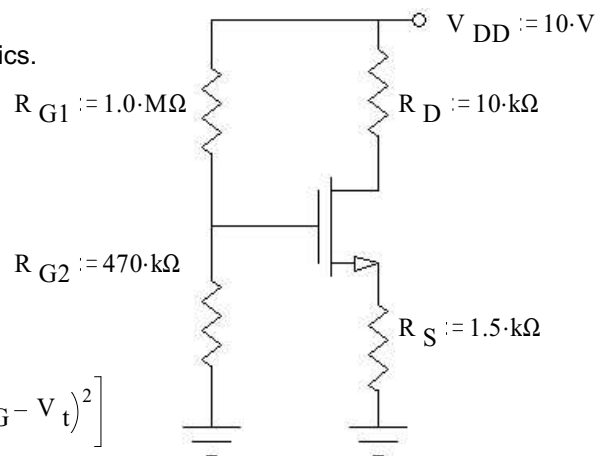
$$V_{GS} := V_G - V_S$$

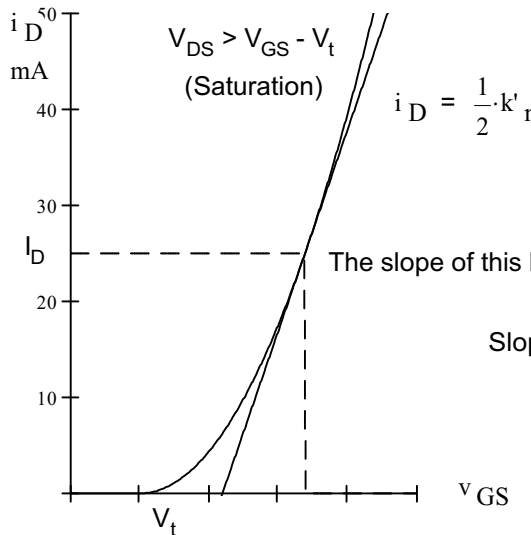
$$V_{GS} = 2.397 \cdot V$$

$$V_{DS} := V_D - V_S$$

$$V_{DS} = 3.861 \cdot V > V_{GS} - V_t = 0.597 \cdot V$$

Saturation region





The slope of this line at the bias point is the "linearization" about the bias point.

$$\text{Slope} = \frac{d}{dv_{GS}} i_D = \frac{d}{dv_{GS}} \left[ \frac{1}{2} \cdot k'_n \cdot \frac{W}{L} \cdot (v_{GS} - V_t)^2 \right]$$

$$= \left[ k'_n \cdot \frac{W}{L} \cdot (v_{GS} - V_t) \right] \cdot 1 = g_m = \frac{i_d}{v_{gs}}$$

small signal values

$$g_m = k'_n \cdot \frac{W}{L} \cdot (V_{GS} - V_t) = \sqrt{k'_n \cdot \frac{W}{L} \cdot 2 \cdot I_D}$$

$$= \sqrt{\frac{4 \cdot I_{DSS} \cdot I_D}{V_t^2}} \quad \text{Depletion-type parts}$$

Also called "transfer admittance,  $y_f$ "

Use  $\frac{1}{g_m}$  in gain equations like  $r_e$  for BJT's

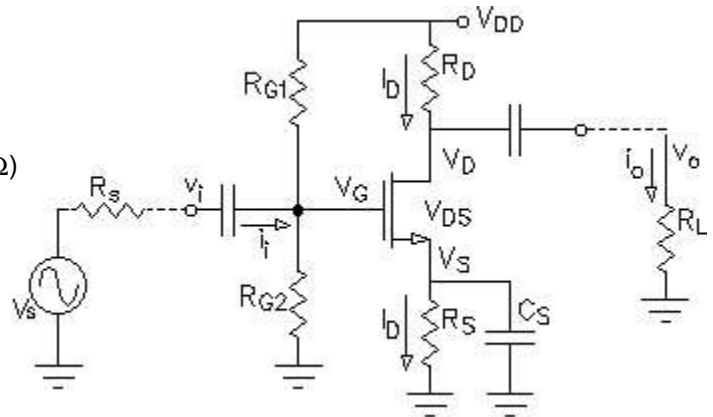
Common-source amp

DC bias:  $V_G = \frac{R_{G2}}{R_{G1} + R_{G2}}$

$I_G = 0$ , so  $R_{G1}$  and  $R_{G2}$  can be very large (typ  $\geq 1 \text{ M}\Omega$ )

$V_S = R_S \cdot I_D$

$V_D = V_{DD} - R_D \cdot I_D$



Input impedance:  $R_i = R_{G1} \parallel R_{G2}$

Except at high frequencies, the input impedance to the MOSFET itself can be considered  $\infty$

Output impedance:  $R_o = R_D \parallel r_o$  <--- Often neglected:  $r_o = \frac{V_A}{I_D} = \frac{1}{\lambda \cdot I_D}$

Early voltage.

AC collector resistance:  $r_d = R_D \parallel R_L \parallel r_o$

Voltage gain:  $A_v = \frac{v_o}{v_g} = g_m \cdot r_d$

Unloaded voltage gain:  $A_{v0} = g_m \cdot R_o$

This is not a very linear amplifier, especially with large output signals, however, the swing limits are:

Clipping

Maximum output swings before clipping: + swing:  $L+ = I_D \cdot r_d$     - swing:  $L- = \frac{V_D - V_G + V_t}{1 + \frac{1}{A_v}}$

$V_{oppmax}$  is smaller of:  $2L+$  or  $2L-$